			<u>,</u>	
L Numbe			DB	Time stamp
1	. 12731	packag\$3 same (chip\$1 die\$1 dice\$1) and	USPAT;	2004/03/12 09:48
		(multiple multi) adj5 (module\$1 layer\$2)	US-PGPUB;	
			EPO; JPO	
2	2397	(packag\$3 same (chip\$1 die\$1 dice\$1) and	USPAT;	2004/03/12 10:02
		(multiple multi) adj5 (module\$1 layer\$2))	US-PGPUB;	
		and (pcb\$2 circuit\$1 adj board\$1) near20	EPO; JPO	
		(si silicon semiconductor polysilicon)		
3	278	((packag\$3 same (chip\$1 die\$1 dice\$1)	USPAT;	2004/03/12 09:53
		and (multiple multi) adj5 (module\$1	US-PGPUB;	
		layer\$2)) and (pcb\$2 circuit\$1 adj	EPO; JPO	
İ		board\$1) near20 (si silicon semiconductor		
		polysilicon)) and (pcb\$2 circuit\$1 adj		
		board\$1) near7 (si silicon semiconductor		
İ		polysilicon) and high adj frequency		
4	113	(((packag\$3 same (chip\$1 die\$1 dice\$1)	USPAT;	2004/03/12 10:02
		and_(multiple_multi) adj5 (module\$1	US-PGPUB;	+ -
		layer\$2)) and (pcb\$2 circuit\$1 adj	EPO; JPO	
		board\$1) near20 (si silicon semiconductor		
		polysilicon)) and (pcb\$2 circuit\$1 adj		
		board\$1) near7 (si silicon semiconductor		
		polysilicon) and high adj frequency) and		:
		signal same power same ground		
5	.113	(((packag\$3 same (chip\$1 die\$1 dice\$1)	ÚSPAT;	2004/03/12 10:02
ĺ		and (multiple multi) adj5 (module\$1	US-PGPUB;	2001,00,12 20.02
		layer\$2)) and (pcb\$2 circuit\$1 adj	EPO; JPO	
		board\$1) near20 (si silicon semiconductor	210, 010	
		polysilicon)) and (pcb\$2 circuit\$1 adj		i
		board\$1) near7 (si silicon semiconductor		
	-	polysilicon) and high adj frequency) and		
		signal same power same ground) and (pcb\$2		
		circuit\$1 adj board\$1) near7 (si silicon		
		semiconductor polysilicon)	1	1
1	1	Semiconductor porysiticon)	1	